IN THE CLAIMS:

1. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~ located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a different potential difference continuous application step of~~ continuously applying a potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate.

2. (Currently Amended) A liquid crystal device having a driving circuit to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~ located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode is

~~formed~~located, ~~to a bend configuration,~~ the liquid crystal device comprising:

different potential difference continuous application means for continuously applying a potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate.

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3. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, gate lines and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a primary potential difference application step of~~ applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the

pixel electrode on the first substrate and the opposing electrode on the second substrate;

~~a secondary potential difference application step of~~ applying a secondary potential difference smaller than the primary potential difference; and

~~a repeat control step of~~ alternately ~~executing~~ applying a ~~the~~ primary potential difference ~~application step~~ and ~~the~~ applying a secondary potential difference ~~application step~~ at least one time each during a ~~repeated~~ repeatable cycle period, the length of a primary potential difference application period being ~~in the range of~~ from at least 50% ~~or more~~ to no more than 95% ~~or less~~ of the length of one ~~repeated~~ repeatable cycle period.

4. (Currently Amended) The method for driving a liquid crystal device according to claim 3, ~~which comprises~~further comprising ~~a period switching control step of~~ controlling the time required for switching ~~of~~ the potential difference to be no more than 30% ~~or less~~ of a single ~~period of one repeated~~ repeatable cycle period when the primary potential difference

and the secondary potential difference are alternately applied ~~in~~ at least one time during said single period ~~the repeat control step~~.

5. (Currently Amended) A method for driving a liquid crystal device, wherein ~~the different potential difference continuous application step according to claim 1 and the~~ applying a primary potential difference ~~application step~~ according to claim 3 ~~are a common electrode potential variation using different potential difference continuous application step and~~ comprises varying a common electrode potential ~~variation using~~ by continuously applying a primary potential difference ~~continuous application step, respectively~~, wherein storage capacities connected to the pixel electrodes are ~~formed~~ located between the pixel electrodes and common electrodes having potentials common to all the pixel electrodes, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin-film transistors ~~parasitic gate lines~~ and the pixel electrodes, potential variation of the pixel electrodes

accompanied by ~~the~~ potential variation of the common electrodes ~~is used to obtain~~ results in the potential difference.

6. (Currently Amended) The method for driving a liquid crystal device according to claim 5, ~~wherein the common electrode potential variation using different potential difference continuous application step and the~~ varying a common electrode potential ~~variation using primary potential difference continuous application step are each a step of~~ comprises making voltage applied to the common electrodes equal to voltage used for gate signals.

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7. (Currently Amended) A method for driving a liquid crystal device, wherein ~~the different potential difference continuous application step according to claim 1 and the~~ applying a primary potential difference ~~application step~~ according to claim 3 ~~are a gate line potential variation using different potential difference continuous application step and~~ comprises varying a gate line potential ~~variation using by~~ continuously applying a primary potential difference ~~continuous~~

~~application step, respectively~~, wherein storage capacities connected to the pixel electrodes are ~~formed~~ located between the pixel electrodes and the gate lines one line front or behind, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin-film transistors ~~parasitic gate lines~~ and the pixel electrodes, potential variation of the pixel electrodes accompanied by ~~the~~ potential variation of the gate lines one line front or behind ~~is used to obtain~~ results in the potential difference.

8. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~ located between a first substrate on which thin film transistors, gate lines and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

primary potential difference application means for applying a primary potential difference, different from a potential differencethat in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate;

secondary potential difference application means for applying a secondary potential difference smaller than the primary potential difference; and

repeat control means of for alternately executing the primary potential difference application means step and the secondary potential difference application means step at least one time each during a repeated period, the length of a primary potential difference application period being in the range of from at least 50% or more to no more than 95% or less of the a length of one repeated period.

9. (Currently Amended) The driving circuit of the liquid crystal device according to claim 8, which comprisesfurther comprising period switching control means for controlling the a time required for switching between the potential difference in

~~the~~ a primary potential difference application period and the potential difference in ~~the~~ a secondary potential difference application period to be no more than 30% ~~or less~~ of a single period of one repeated period when the primary potential difference and the secondary potential difference are alternately applied in the repeat control means.

10. (Currently Amended) A driving circuit of a liquid crystal device, wherein ~~the different potential difference continuous application means according to claim 2 and~~ the primary potential difference application means according to claim 8 ~~are~~ comprises ~~a common electrode potential variation using different potential difference continuous application means and~~ means for varying a common electrode potential ~~variation~~ by using means for continuously applying a primary potential difference ~~continuous application means, respectively~~, wherein storage capacities connected to the pixel electrodes are ~~formed~~ located between the pixel electrodes and common electrodes having potentials common to all the pixel electrodes, so that, by means of a ratio between pixel electrode capacities

including the storage capacities and capacities between parasitic gate lines of the thin-film transistors ~~parasitic gate lines~~ and the pixel electrodes, potential variation of the pixel electrodes accompanied by ~~the~~ potential variation of the common electrodes is used to obtain the potential difference.

11. (Currently Amended) The driving circuit of the liquid crystal device according to claim 10, wherein ~~the common electrode potential variation using different potential difference continuous application means and~~ the means for varying common electrode potential ~~variation~~ by using means for continuously applying a primary potential difference ~~continuous application means are each~~ comprises means for making voltage applied to the common electrodes equal to voltage used for gate signals.

12. (Currently Amended) A driving circuit of a liquid crystal device, wherein ~~the different potential difference continuous application means according to claim 2 and~~ the primary potential difference application means according to

claim 8 ~~are~~ comprises ~~a gate line potential variation using different potential difference continuous application means and a~~ means for varying a gate line potential ~~variation by~~ using means for continuously applying a primary potential difference ~~continuous application means, respectively~~, wherein storage capacities connected to the pixel electrodes are ~~formed~~ located between the pixel electrodes and the gate lines one line front or behind, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin-film transistors ~~parasitic gate lines~~ and the pixel electrodes, potential variation of the pixel electrodes accompanied by ~~the~~ potential variation of the gate lines one line front or behind ~~is used to obtain~~ results in the potential difference.

13. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, gate lines and pixel electrodes are ~~formed~~ located

in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a primary potential difference application step of~~ applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode and the opposing electrode;

~~a secondary potential difference application step of~~ applying a secondary potential difference smaller than the primary potential difference;

~~a repeat control step of~~ alternately executing ~~the primary potential difference application step and the secondary potential difference application step~~ applying a primary potential difference and applying a secondary potential difference at least one time each; and

~~a charging sub-step of~~ applying to source lines a potential in which a pixel electrode potential variation is reflected in ~~the~~ an opposing electrode potential, the pixel electrode potential variation being induced by ~~the~~ potential variation of the gate lines when the pixel transistor is switched to OFF from

ON in ~~the~~ applying a secondary potential difference ~~application step~~, to charge the pixel electrodes.

14. (Currently Amended) The method for driving the liquid crystal device according to claim 13, wherein ~~the~~ applying a secondary potential difference ~~application step allows~~ sets the secondary potential difference ~~to be set to be~~ within ~~the~~ a range of ±1 V.

15. (Currently Amended) The method for driving the liquid crystal device according to claim 13, wherein ~~the~~ applying a secondary potential difference ~~application step allows~~ applies a potential equal to ~~that of~~ a potential of the opposing electrode ~~to be applied~~ to the source lines when the pixel transistors are OFF in ~~the~~ a period ~~in~~ during which the secondary potential difference is applied.

16. (Currently Amended) The method for driving the liquid crystal device according to claim 13, wherein ~~the charging sub-step~~ applying a potential to source lines is performed at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration.

17. (Currently Amended) The method for driving the liquid crystal device according to claim 13, wherein ~~the charging sub-step~~ applying a potential to source lines is performed at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration, in ~~the~~ an initial stage ~~of~~ during which ~~the~~ applying a primary potential difference ~~application step~~ and ~~the~~ applying a secondary potential difference ~~application step~~ are initiated.

18. (Currently Amended) The method for driving the liquid crystal device according to claim 13, further comprising ~~which comprises a gate line off-voltage direct current holding step of~~ holding ~~an~~ a direct current off-voltage ~~of~~ in the gate line ~~in direct current~~.

19. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, gate lines and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

primary potential difference application means for applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode and the opposing electrode;

secondary potential difference application means for applying a secondary potential difference smaller than the primary potential difference;

repeat control means for alternately operating the primary potential difference application means and the secondary potential difference application means at least one time each; and

charging ~~sub-~~means for applying to source lines a potential in which a pixel electrode potential variation is reflected in ~~the~~ an opposing electrode potential, the pixel electrode potential variation being induced by ~~the~~ potential variation of the gate lines when the pixel transistor is switched to OFF from ON in ~~the~~ a secondary potential difference application period, to charge the pixel electrodes.

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20. (Currently Amended) The driving circuit of the liquid crystal device according to claim 19, wherein the secondary potential difference application means ~~allows~~ is for applying the secondary potential difference ~~to be set to be~~ within ~~the~~ a range of ±1 V.

21. (Currently Amended) The driving circuit of the liquid crystal device according to claim 19, wherein the secondary potential difference application means ~~allows~~ is for applying a potential equal to ~~that of~~ a potential of the opposing electrode ~~to be applied~~ to the source lines when the pixel transistors are

OFF in ~~the~~ a period ~~in~~ during which the secondary potential difference is applied.

22. (Currently Amended) The driving circuit of the liquid crystal device according to claim 19, ~~wherein~~ further comprising means for operating the charging ~~sub-~~means ~~is operated~~ at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration.

23. (Currently Amended) The driving circuit of the liquid crystal device according to claim 19, ~~wherein~~ further comprising means for operating the charging ~~sub-~~means ~~is operated~~ at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration, in ~~the~~ an initial stage ~~of~~ during which the primary potential difference application means and the secondary potential difference application means are initiated.

24. (Currently Amended) The driving circuit of the liquid crystal device according to claim 19, ~~which comprises~~further comprising gate line off-voltage direct current holding means for holding ~~an~~ a direct current off-voltage ~~of~~ in the gate line ~~in direct current~~.

25. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, gate lines and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a primary potential difference application step of~~ applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode and the opposing electrode;

~~a secondary potential difference application step of~~ applying a secondary potential difference smaller than the primary potential difference;

~~a repeat control step of~~ alternately executing ~~the~~ applying a primary potential difference ~~application step~~ and ~~the~~ applying a secondary potential difference ~~application step~~ at least one time each; and

~~a charging sub-step of~~ applying to source lines a potential in which a pixel electrode potential variation is reflected in the opposing electrode potential, the pixel electrode potential variation being induced by ~~the~~ a potential variation of the gate lines when the pixel transistor is switched to OFF from ON ~~in the~~ while applying a secondary potential difference ~~application step~~, to charge the pixel electrodes,

wherein the potential of the source lines is modulated to a potential different from a potential difference~~that~~ in a period ~~in~~ during which the secondary potential difference is applied so that the primary potential difference can be further increased in a period ~~in~~ during which the primary potential difference is applied.

26. (Currently Amended) The method for driving the liquid crystal device according to claim 25, wherein ~~the~~ applying a secondary potential difference ~~application step allows~~ applies the secondary potential difference ~~to be set to be~~ within the range of ±1 V.

27. (Currently Amended) The method for driving the liquid crystal device according to claim 25, wherein ~~the~~ applying a secondary potential difference ~~application step allows~~ applies a potential equal to ~~that of~~ a potential of the opposing electrode ~~to be applied~~ to the source lines when the pixel transistors are OFF in ~~the~~ a period ~~in~~ during which the secondary potential difference is applied.

28. (Currently Amended) The method for driving the liquid crystal device according to claim 25, ~~wherein the charging sub-step is performed~~comprising applying a potential to source lines at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration.

29. (Currently Amended) The method for driving the liquid crystal device according to claim 25, ~~wherein the charging sub-step is performed~~ comprising applying a potential to source lines at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration, in the initial stage of which ~~the~~ applying a primary potential difference ~~application step~~ and ~~the~~ applying a secondary potential difference ~~application step~~ are initiated.

30. (Currently Amended) The method for driving the liquid crystal device according to claim 25, which comprises ~~a gate line off-voltage direct current holding step of~~ holding ~~an~~ a direct current off-voltage of the gate line ~~in direct current~~.

31. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, gate lines and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

primary potential difference application means for applying a primary potential difference, different from a potential difference ~~that~~ in a normal image display period, between the pixel electrode and the opposing electrode;

secondary potential difference application means for applying a secondary potential difference smaller than the primary potential difference;

repeat control means for alternately operating the primary potential difference application means and the secondary potential difference application means at least one time each; and

charging ~~sub-~~means ~~of~~ for applying to source lines a potential in which a pixel electrode potential variation is refleçted in the opposing electrode potential, the pixel electrode potential variation being induced by ~~the~~ a potential variation of the gate lines when the pixel transistor is switched to OFF from ON in the secondary potential difference application period, to charge the pixel electrodes,

wherein the potential of the source lines is modulated to a potential different from a potential difference~~that~~ in a period ~~in~~ during which the secondary potential difference is applied so that the primary potential difference can be further increased in a period ~~in~~ during which the primary potential difference is applied.

32. (Currently Amended) The driving circuit of the liquid crystal device according to claim 31, wherein the secondary potential difference application means ~~allows~~ is for applying the secondary potential difference ~~to be set to be~~ within the range of ±1 V.

33. (Currently Amended) The driving circuit of the liquid crystal device according to claim 31, wherein the secondary potential difference application means ~~allows~~ is for applying a potential equal to a potential of ~~that of~~ the opposing electrode ~~to be applied~~ to the source lines when the pixel transistors are OFF in the period ~~in~~ during which the secondary potential difference is applied.

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34. (Currently Amended) The driving circuit of the liquid crystal device according to claim 31, wherein the charging ~~sub-~~ means is ~~operated~~ for operating at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration.

35. (Currently Amended) The driving circuit of the liquid crystal device according to claim 31, wherein the charging ~~sub-~~ means is ~~operated~~ for operating at least once in an initial stage of a driving period for ~~the~~ transition of the liquid crystal layer to the bend configuration, in ~~the~~ an initial stage of which the primary potential difference application means and

the secondary potential difference application means are initiated.

36. (Currently Amended) The driving circuit of the liquid crystal device according to claim 31, which comprises gate line off-voltage direct current holding means for holding ~~an~~ a direct current off-voltage of the gate line ~~in direct current~~.

37. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a primary potential difference application step of~~ applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the

pixel electrode on the first substrate and the opposing electrode on the second substrate; and

~~a secondary potential difference application step of~~ applying a secondary potential difference smaller than the primary potential difference;

~~a repeat control step of~~ alternately controlling ~~the~~ applying a primary potential difference ~~application step~~ and ~~the~~ applying a secondary potential difference ~~application step~~ at least one time each,

wherein ~~in the repeat control step~~during alternately controlling applying a primary potential difference and applying a secondary potential difference, ~~the~~ applying a secondary potential difference ~~application step~~ is performed first.

38. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is~~

~~formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

primary potential difference application means for applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate;

secondary potential difference application means for applying a secondary potential difference smaller than the primary potential difference; and

repeat control means for allowing the secondary potential difference application means to operate first and allowing the primary potential difference application means and the secondary potential difference application means to alternately operate at least one time each.

39. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film

transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a primary potential difference application step of~~ applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate; ~~and~~

~~a secondary potential difference application step of~~ applying a secondary potential difference smaller than the primary potential difference;

~~a repeat control step of~~ alternately executing ~~the~~ applying a primary potential difference ~~application step~~ and ~~the~~ applying a secondary potential difference ~~application step~~ at least one time each; and

~~a high-potential-difference-for-transition application step of~~ applying a larger potential difference, of the potential differences applied to the liquid crystal layer in the normal image information display period, to the liquid crystal layer at

least one field during a period from after completion of ~~the~~ alternate execution of ~~the~~ applying a primary potential difference ~~application step~~ and the applying a secondary potential difference ~~application step~~ at least one time each until the shift to the normal image information display period is achieved.

40. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

primary potential difference application means for applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate; and

secondary potential difference application means for applying a secondary potential difference smaller than the primary potential difference;

means for ~~repeat control step of~~ alternately controlling the primary potential difference application means and the secondary potential difference application means at least one time each, and

high-potential-difference-for-transition application means for applying a relatively larger potential difference~~,~~ of the potential differences applied to the liquid crystal layer in the normal image information display period, to at least one field of the liquid crystal layer ~~at least one field~~ during a period from after completion of ~~the alternate~~ alternately executing of ~~the~~ said means for applying a primary potential difference ~~application step~~ and ~~the~~ said means for applying a secondary potential difference ~~application step~~ at least one time each until the shift to the normal image information display period is achieved.

41. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a primary potential difference application step of~~ applying a primary potential difference, different from ~~that~~a potential difference in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate;

~~a secondary potential difference application step of~~ applying a secondary potential difference smaller than the primary potential difference;

~~a repeat control step of~~ allowing ~~the~~ applying a secondary potential difference application ~~step~~ to be initiated first, and alternately operating ~~the~~ applying a primary potential difference ~~application step~~ and ~~the~~ applying a secondary

potential difference ~~application step~~ at least one time each, and

~~an activation controlling step of~~ controlling activation of parts of the liquid crystal device in advance, to keep the aligned state of the liquid crystal layer from being disarranged to an excessive degree after power is turned on.

42. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors and pixel electrodes are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

primary potential difference application means for applying a primary potential difference, different from a potential difference~~that~~ in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate;

secondary potential difference application means for applying a secondary potential difference smaller than the primary potential difference;

repeat control means for allowing the means for secondary potential difference ~~application step~~ to be initiated first, and alternately operating the means for primary potential difference ~~application means~~ and the means for secondary potential difference ~~application means~~ at least one time each, and

activation controlling means for controlling activation of parts of the liquid crystal device in advance, to keep ~~the~~ an aligned state of the liquid crystal layer from being disarranged to an excessive degree after power is turned on.

43. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, pixel electrodes, gate lines, and others are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an

opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a high potential difference application step of~~ providing a period ~~in~~ during which a larger potential difference than a potential difference in a normal image display period is applied between the pixel electrode and the opposing electrode, while scanning the gate lines by using pulsed signals.

44. (Currently Amended) A driving circuit of a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, pixel electrodes, gate lines, and others are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the driving circuit comprising:

high potential difference application means for providing a period ~~in~~ during which a larger potential difference than a potential difference in a normal image display period is applied

between the pixel electrode and the opposing electrode, while scanning the gate lines by using pulsed signals.

45. (Currently Amended) A method for driving a liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer, ~~provided~~located between a first substrate on which thin film transistors, gate lines, pixel electrodes, and others are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ the method comprising:

~~a high electric field applied activation step of~~ applying an electric field~~, higher than that applied to the liquid crystal layer in the normal image display period,~~ between the liquid crystal layer located between the gate line on the first substrate and the opposing electrode on the second substrate, the electric field being higher than an electric field applied to the liquid crystal layer in other regions of the liquid crystal device.

46. (Currently Amended) A liquid crystal device to cause transition ~~of~~ from a splay configuration to a bend configuration of a liquid crystal layer~~, provided~~ located between a first substrate on which thin film transistors, pixel electrodes, and gate lines ~~and others~~ are ~~formed~~ located in a matrix ~~form~~ and a second substrate on which an opposing electrode ~~is formed~~is located, ~~to a bend configuration,~~ comprising:

~~wherein there is a period in which~~ means for applying an electric field ~~higher than that applied to the liquid crystal layer in the normal image display period is applied~~ between the liquid crystal layer located between the gate line on the first substrate and the opposing electrode on the second substrate, the electric field being higher than an electric field applied to the liquid crystal layer in other regions of liquid crystal device.

47. (Currently Amended) The liquid crystal device according to claim 46, wherein the gate line on the first substrate is a strong electric field applied gate line which ~~is formed to have~~ has an insulating layer reduced in thickness at a portion where no other metal layer or no semiconductor layer is present between the gate line and the liquid crystal layer.

48. (Currently Amended) The liquid crystal device according to claim 46, wherein the insulating layer between the gate line on the first substrate and the liquid crystal layer ~~is~~ comprises a high specific inductive capacity insulating layer made of a material ~~using material of high~~ a specified specific inductive capacity.

49. (Currently Amended) The liquid crystal device according to claim 46, wherein the gate line on the first substrate is an at-specific-part-thickened gate line which ~~is formed~~is located to have an increased metal thickness at a portion where no other metal layer or no semiconductor layer is present between the gate line and the liquid crystal layer.

50. (Currently Amended) The liquid crystal device according to claim 46, wherein the gate line on the first substrate ~~is~~ comprises a partly contacted gate line in which a source line forming metal is laminated on a gate line forming metal in electric contact therewith at a portion where no other metal layer or no semiconductor layer is present between the gate line and the liquid crystal layer.

51. (Currently Amended) The liquid crystal device according to claim 46, wherein the gate line on the first substrate ~~is~~ comprises a partly contacted gate line in which a source line forming metal is laminated on a gate line forming metal not in electric contact therewith at a portion where no other metal layer or no semiconductor layer is present between the gate line and the liquid crystal layer.

52. (Currently Amended) The liquid crystal device according to claim 46, wherein the opposing electrode on the second substrate ~~is~~ comprises a divided opposing electrode that is divided into a part confronting the gate line on the first substrate and the remaining part.

53. (Currently Amended) The liquid crystal device according to claim 46, wherein the opposing electrode on the second substrate ~~is~~ comprises an at-confronting-portion thickened opposing electrode that ~~is formed~~is located to be larger in thickness at a portion confronting the gate line on the first substrate than at a non-confronting portion.

54. (Currently Amended) The liquid crystal device according to claim 46, wherein the second substrate has a color filter formed of resin laminated thereon at ~~its~~ a portion ~~confronting~~ adjacent the gate line on the first substrate.

55. (Currently Amended) The liquid crystal device according to claim 54, wherein the color filter ~~formed of resin laminated on the second substrate at its portion confronting the gate line on the first substrate is~~ comprises a color filter ~~formed by~~ comprising a plurality of different color filters ~~being~~ laminated together at ~~their~~ peripheries of the color filters.

56. (Currently Amended) The liquid crystal device according to claim 46, ~~wherein~~ comprising a pillar-shaped spacer ~~is formed~~located on the second substrate at ~~its~~ a portion of the second substrate adjacent ~~confronting~~ the gate line on the first substrate ~~to confront the gate line across the liquid crystal layer~~.

57. (Currently Amended) The liquid crystal device according to claim 56, wherein the pillar-shaped spacer ~~has~~ comprises a pillar-shaped spacer means for applying a potential, ~~application means~~ which is conductive at least ~~at~~ on a liquid crystal layer side thereof, and ~~applies~~ for applying a potential

equivalent to the gate line to the pillar-shaped spacer at a startup of the liquid crystal device.

58. (New) A method for driving a liquid crystal device to cause transition from a splay configuration to a bend configuration of a liquid crystal layer, located between a first substrate on which thin film transistors and pixel electrodes are located in a matrix and a second substrate on which an opposing electrode is located, the method comprising:

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continuously applying a potential difference, different from a potential difference in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate, wherein,

storage capacities connected to the pixel electrodes are formed between the pixel electrodes and common electrodes having potentials common to all the pixel electrodes, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin film transistors and the pixel electrodes, potential variation of the pixel electrodes accompanied by potential

variation of the common electrodes results in a potential difference.

59. (New) A method for driving a liquid crystal device to cause transition from a splay configuration to a bend configuration of a liquid crystal layer, located between a first substrate on which thin film transistors and pixel electrodes are located in a matrix and a second substrate on which an opposing electrode is located, the method comprising:

continuously applying a potential difference, different from a potential difference in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate, wherein,

storage capacities connected to the pixel electrodes are formed between the pixel electrodes and the gate lines one line front or behind, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin-film transistors and the pixel electrodes, potential variation of the pixel electrodes accompanied by potential variation of the gate

lines one line front or behind results in the potential difference.

60. (New) A liquid crystal device having a driving circuit to cause transition from a splay configuration to a bend configuration of a liquid crystal layer, located between a first substrate on which thin film transistors and pixel electrodes are located in a matrix and a second substrate on which an opposing electrode is located, to a bend configuration, the liquid crystal device comprising:

different potential continuous application means for continuously applying a potential difference, different from a potential difference in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate, wherein

the different potential difference continuous application means comprises means for varying a common electrode potential by using means for continuously applying a different potential difference, wherein storage capacities connected to the pixel electrodes are formed between the pixel electrodes and common

electrodes having potentials common to all the pixel electrodes, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin-film transistors and the pixel electrodes, potential variation of the pixel electrodes accompanied by potential variation of the common electrodes results in a potential difference.

61. (New) A liquid crystal device having a driving circuit to cause transition from a splay configuration to a bend configuration of a liquid crystal layer, located between a first substrate on which thin film transistors and pixel electrodes are formed in a matrix and a second substrate on which an opposing electrode is located, the liquid crystal device comprising:

different potential difference continuous application means for continuously applying a potential difference, different from a potential difference in a normal image display period, between the pixel electrode on the first substrate and the opposing electrode on the second substrate, wherein,

the different potential difference continuous application means comprises means for varying a gate line potential by using means for continuously applying a different potential difference, wherein storage capacities connected to the pixel electrodes are formed between the pixel electrodes and the gate lines one line front or behind, so that, by means of a ratio between pixel electrode capacities including the storage capacities and capacities between parasitic gate lines of the thin-film transistors and the pixel electrodes, potential variation of the pixel electrodes accompanied by the potential variation of the gate lines one line front or behind results in a potential difference.

62. (New) The method of driving a liquid crystal according to claim 58, wherein continuously varying a common electrode potential by continuously applying a different potential difference comprises making voltage applied to the common electrodes equal to voltage used for gate signals.

63. (New) The method of driving a liquid crystal according to claim 59, wherein continuously varying a common electrode potential by continuously applying a different potential difference comprises making voltage applied to the common electrodes equal to voltage used for gate signals.

64. (New) The driving circuit of the liquid crystal device according to claim 60, wherein the means for varying a common electrode potential by using means for continuously applying a different potential difference comprises means for making voltage applied to the common electrodes equal to voltage used for gate signals.